

Claim Listing:

- 1-11. (Cancelled)
12. (Previously Presented) A semiconductor device comprising:
a semiconductor substrate;
a gate line including a gate insulation pattern and a gate electrode which are sequentially stacked on the semiconductor substrate;
a spacer formed on a sidewall of the gate line; and
a conductive line pattern disposed on the gate line; and
an interlayer dielectric on the semiconductor substrate having a top surface that is coplanar with a top surface of the gate line;
wherein the conductive line pattern is parallel to the gate line and electrically connected to the gate electrode.
13. (Original) The semiconductor device of Claim 12, wherein the gate electrode comprises a doped polysilicon layer.
14. (Original) The semiconductor device of Claim 13, further comprising a metal silicide layer, wherein the metal silicide layer is on the doped polysilicon layer.
15. (Original) The semiconductor device of Claim 14, further comprising an interlayer dielectric on the semiconductor substrate that includes a groove that exposes a top surface of the gate line, and wherein the conductive line pattern is provided in the groove.
16. (Original) The semiconductor device of Claim 15, further comprising an etch-stop layer between the semiconductor substrate and the interlayer dielectric, wherein the etch-stop layer has an etch selectivity with respect to the interlayer dielectric.
17. (Cancelled)
18. (Original) The semiconductor device of Claim 12, wherein the conductive line

pattern has at least the same length as the gate line.

19. (Original) The semiconductor device of Claim 12, wherein the conductive line pattern is made of metal.

20. (Original) The semiconductor device of Claim 14, wherein the conductive layer bridges at least one gap in the metal silicide layer.

21. (Original) The semiconductor device of Claim 12, wherein the conductive layer decreases the resistance of the gate electrode.

22. (Original) A semiconductor device comprising:

a semiconductor substrate;

a first gate line and a second gate line on the semiconductor substrate and spaced apart from each other, the first gate line including a first gate electrode stacked on a first gate insulation pattern, and the second gate line including a second gate electrode stacked on a second gate insulation pattern; and

a conductive line pattern on the first and second gate lines, wherein the conductive line pattern has a first portion parallel to the first gate line and a second portion parallel to the second gate line, and wherein the conductive line pattern electrically connects the first and second gate electrodes with each other.

23. (Original) The semiconductor device of Claim 22, wherein the first and second gate lines comprise a doped polysilicon layer.

24. (Original) The semiconductor device of Claim 23, wherein the first and second gate lines further comprise a metal silicide layer on the doped polysilicon layer.

25. (Original) The semiconductor device of Claim 22, further comprising a spacer disposed on a sidewall of the first and second gate lines and an interlayer dielectric covering the semiconductor substrate that includes a groove that exposes top surfaces of the first and

second gate line; and

wherein the conductive line pattern is disposed in the groove in the interlayer dielectric.

26. (Original) The semiconductor device of Claim 25, further comprising an etch-stop layer between the semiconductor substrate and the interlayer dielectric, wherein the etch-stop layer has an etch selectivity with respect to the interlayer dielectric.

27. (Original) The semiconductor device of Claim 22, further comprising an interlayer dielectric on the semiconductor substrate that is planarized to the height of the first and second gate lines.

28. (Original) The semiconductor device of Claim 22, wherein the first portion of the conductive line pattern is at least the same length as the first gate line, and the second portion of the conductive line pattern is at least the same length as the second gate line.

29. (Original) The semiconductor device of Claim 22, wherein the conductive line pattern is made of metal.

30. (Original) The semiconductor device of Claim 24, wherein the conductive layer bridges at least one gap in the metal silicide layer.

31. (Original) The semiconductor device of Claim 22, wherein the conductive layer decreases the resistance of the gate electrode.

32-49. (Canceled).